

International
IR Rectifier

PD - 91670

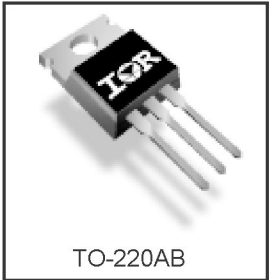
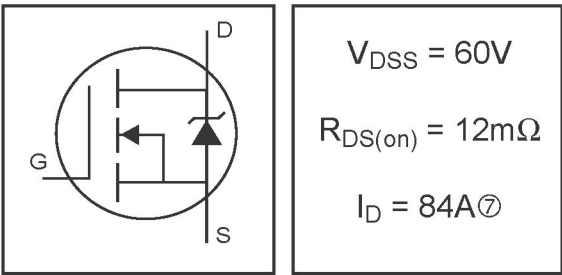
IRF1010E

HEXFET® Power MOSFET

- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated

Description
Advanced HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V$	84⑦	A
$I_D @ T_C = 100^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V$	59	
I_{DM}	Pulsed Drain Current ①	330	
$P_D @ T_C = 25^{\circ}C$	Power Dissipation	200	W
	Linear Derating Factor	1.4	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
I_{AR}	Avalanche Current①	50	A
E_{AR}	Repetitive Avalanche Energy①	17	mJ
dv/dt	Peak Diode Recovery dv/dt ③	4.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Thermal Resistance

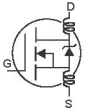
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	---	0.75	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	---	
$R_{\theta JA}$	Junction-to-Ambient	---	62	

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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	60	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.064	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	12	mΩ	V _{GS} = 10V, I _D = 50A ④
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Transconductance	69	—	—	S	V _{DS} = 25V, I _D = 50A④
I _{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	V _{DS} = 60V, V _{GS} = 0V
		—	—	250		V _{DS} = 48V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V
Q _g	Total Gate Charge	—	—	130	nC	I _D = 50A
Q _{gs}	Gate-to-Source Charge	—	—	28		V _{DS} = 48V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	—	44		V _{GS} = 10V, See Fig. 6 and 13
t _{d(on)}	Turn-On Delay Time	—	12	—	ns	V _{DD} = 30V I _D = 50A R _G = 3.6Ω V _{GS} = 10V, See Fig. 10 ④
t _r	Rise Time	—	78	—		
t _{d(off)}	Turn-Off Delay Time	—	48	—		
t _f	Fall Time	—	53	—		
L _D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L _S	Internal Source Inductance	—	7.5	—		
C _{iss}	Input Capacitance	—	3210	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	690	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	140	—		f = 1.0MHz, See Fig. 5
E _{AS}	Single Pulse Avalanche Energy②	—	1180⑤	320⑥		I _{AS} = 50A, L = 260μH



Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	84⑦	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode)①	—	—	330		
V _{SD}	Diode Forward Voltage	—	—	1.3	V	T _J = 25°C, I _S = 50A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	73	110	ns	T _J = 25°C, I _F = 50A
Q _{rr}	Reverse Recovery Charge	—	220	330	nC	di/dt = 100A/μs ④
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Starting T_J = 25°C, L = 260μH
R_G = 25Ω, I_{AS} = 50A, V_{GS} = 10V (See Figure 12)

③ I_{SD} ≤ 50A, di/dt ≤ 230A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 175°C
- ④ Pulse width ≤ 400μs; duty cycle ≤ 2%.

⑤ This is a typical value at device destruction and represents operation outside rated limits.

⑥ This is a calculated value limited to T_J = 175°C .

⑦ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.

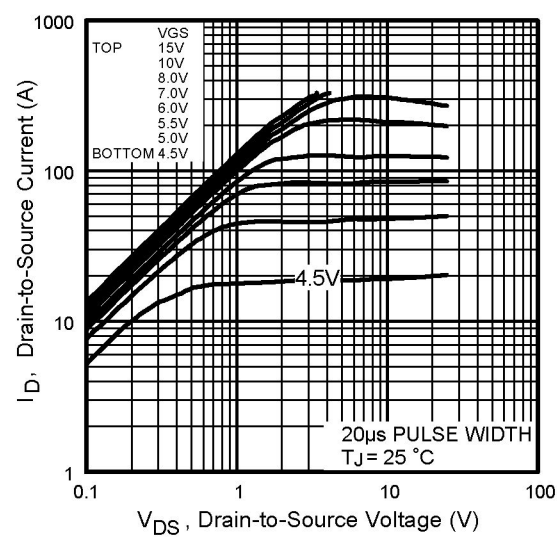


Fig 1. Typical Output Characteristics

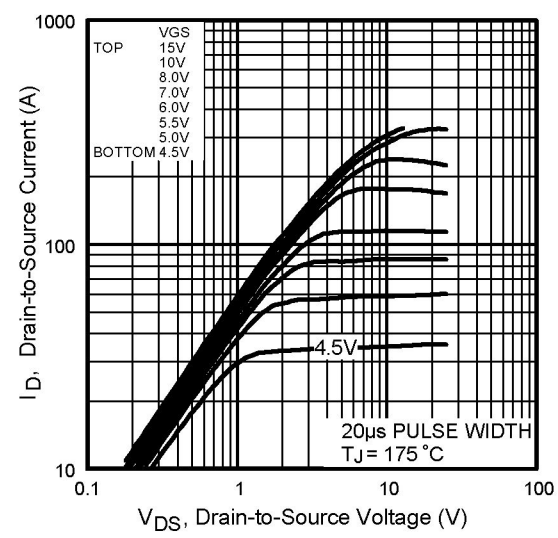


Fig 2. Typical Output Characteristics

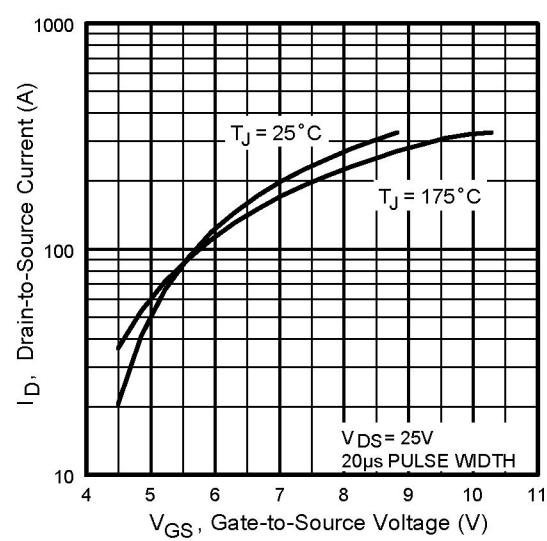


Fig 3. Typical Transfer Characteristics

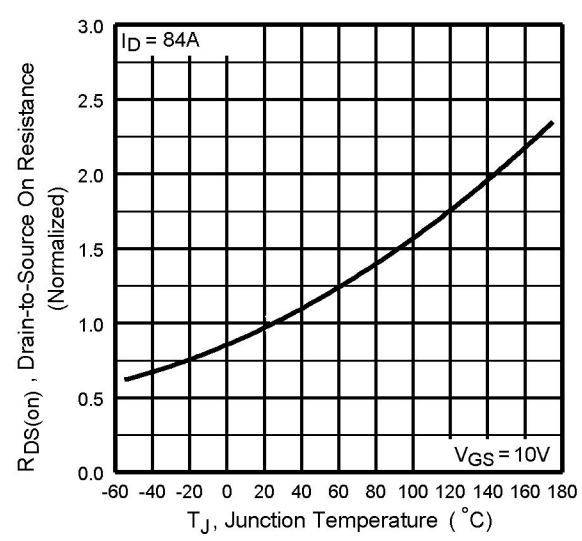


Fig 4. Normalized On-Resistance
Vs. Temperature

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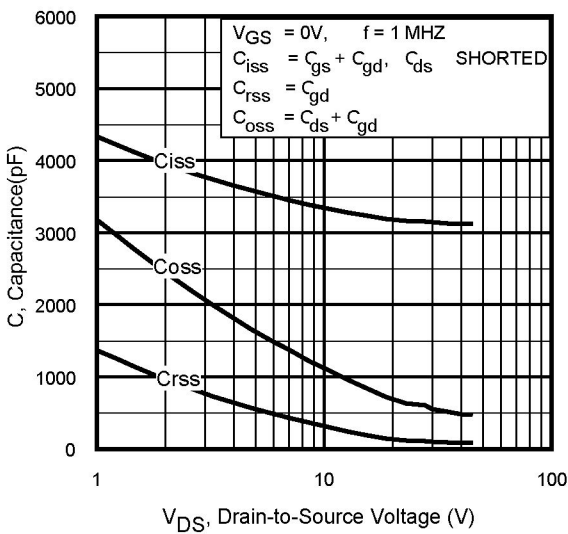


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

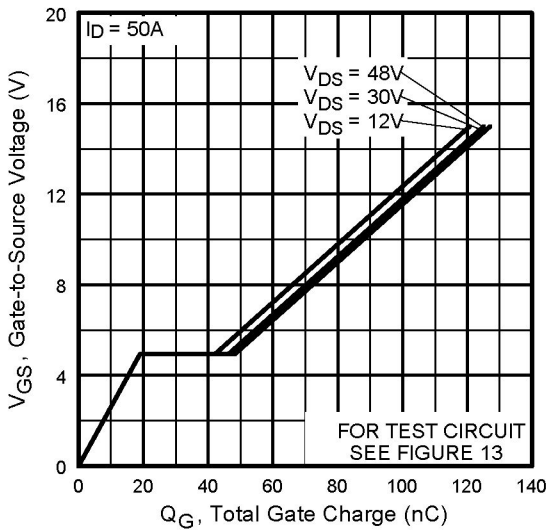


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

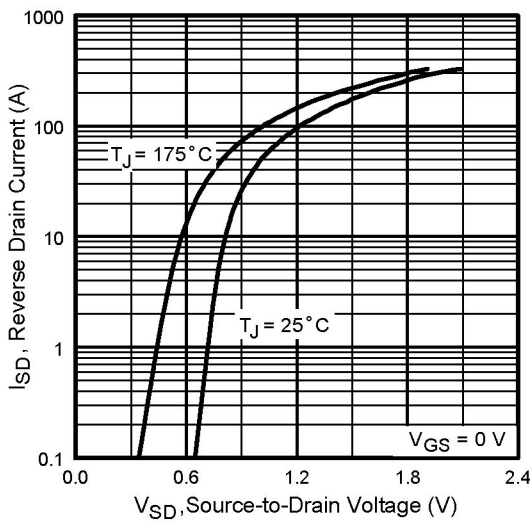


Fig 7. Typical Source-Drain Diode Forward Voltage

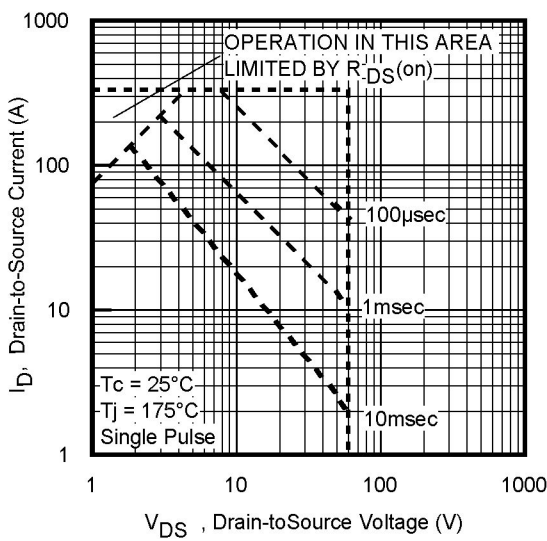


Fig 8. Maximum Safe Operating Area

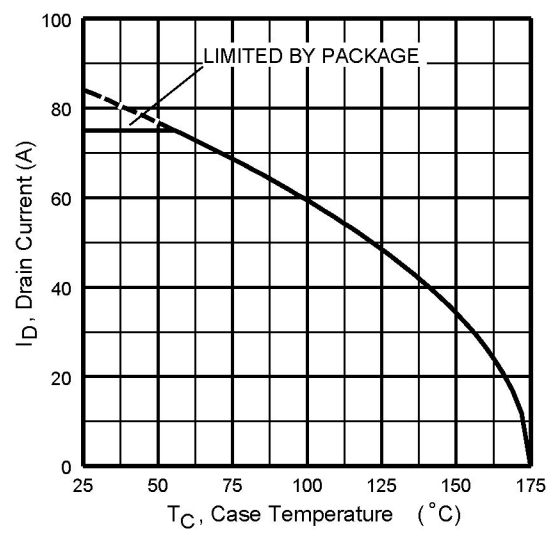


Fig 9. Maximum Drain Current Vs. Case Temperature

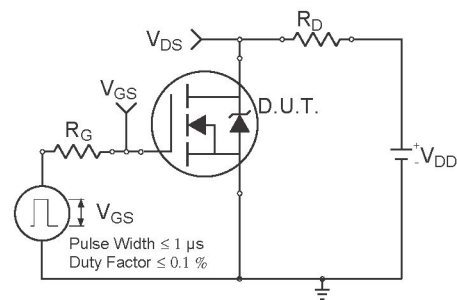


Fig 10a. Switching Time Test Circuit

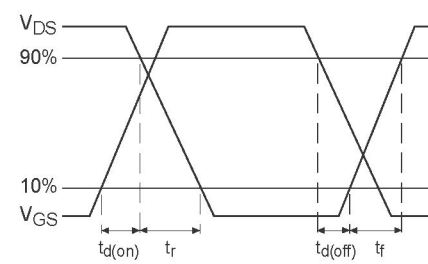


Fig 10b. Switching Time Waveforms

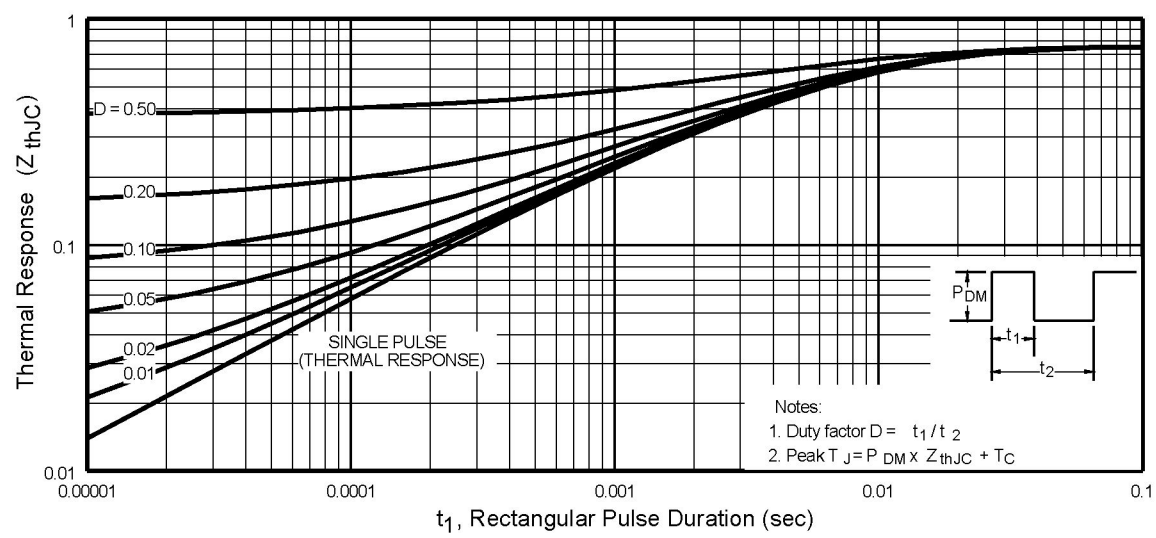


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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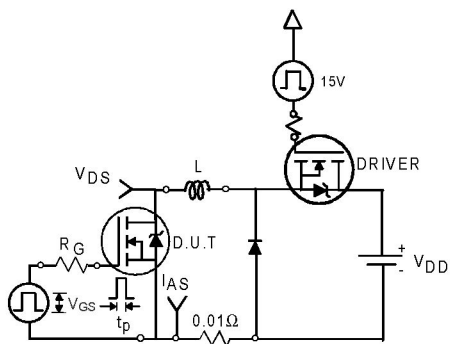


Fig 12a. Unclamped Inductive Test Circuit

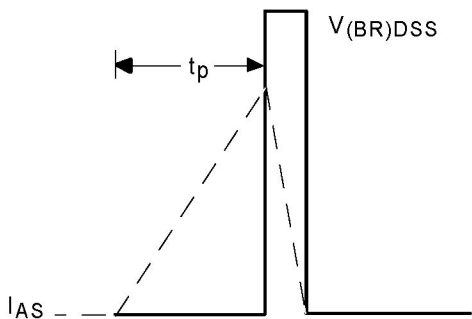


Fig 12b. Unclamped Inductive Waveforms

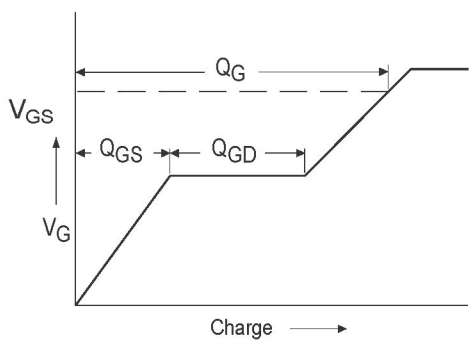


Fig 13a. Basic Gate Charge Waveform

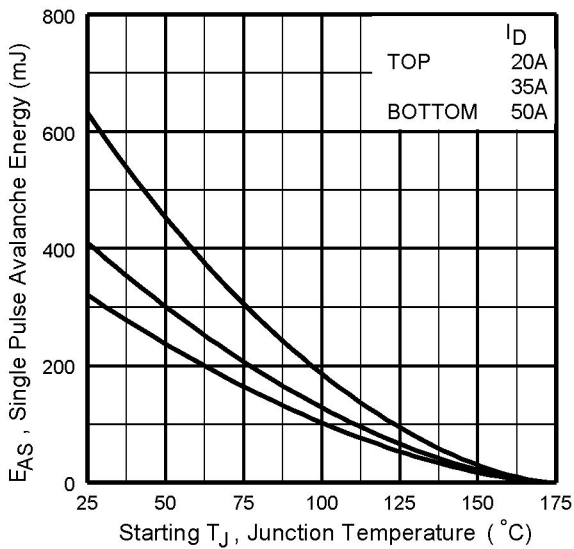


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

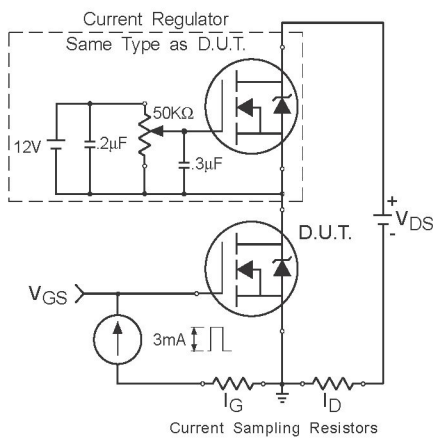


Fig 13b. Gate Charge Test Circuit

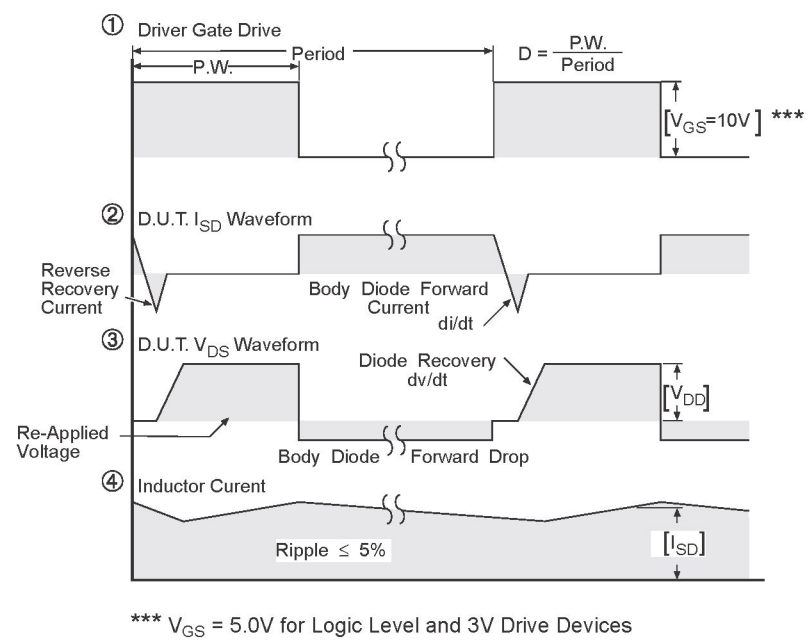
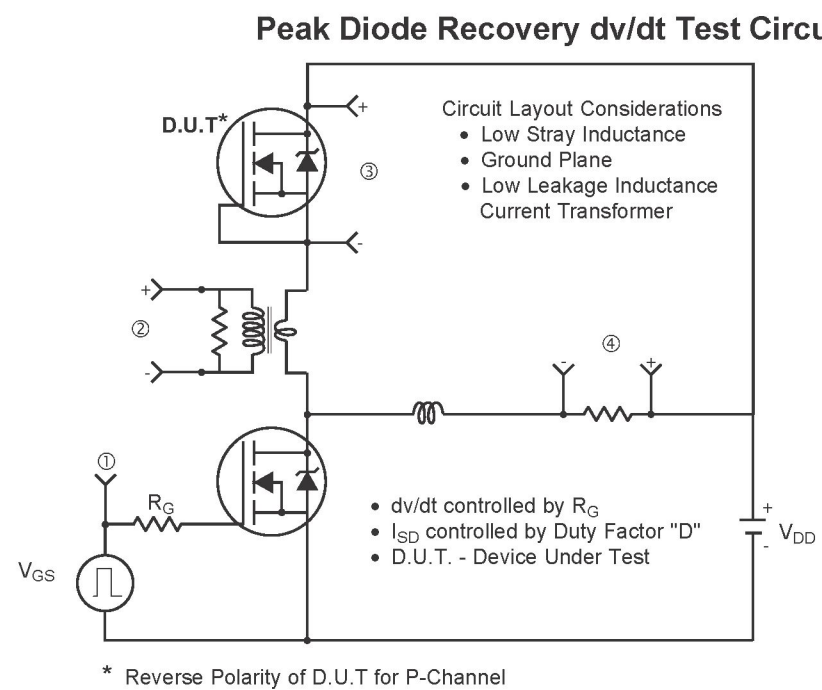


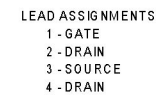
Fig 14. For N-channel HEXFET® power MOSFETs

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Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.	3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
2 CONTROLLING DIMENSION : INCH	4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

TO-220AB

Diagram illustrating the marking on a MOSFET package (IRF1010) and the corresponding labels:

- INTERNATIONAL RECTIFIER LOGO**: Points to the "IR" logo on the package.
- PART NUMBER**: Points to the "1010" part of the marking.
- DATE CODE (YYWW)**: Points to the "9246" marking, which represents the year and week of manufacture.
 - YY = YEAR**: Points to the "92" (Year 1992).
 - WW = WEEK**: Points to the "46" (Week 46).
- ASSEMBLY LOT CODE**: Points to the "9B 1M" marking, which represents the assembly lot.

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Visit us at www.irf.com for sales contact information. 3/01

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